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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	56
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg230f32-qfn64

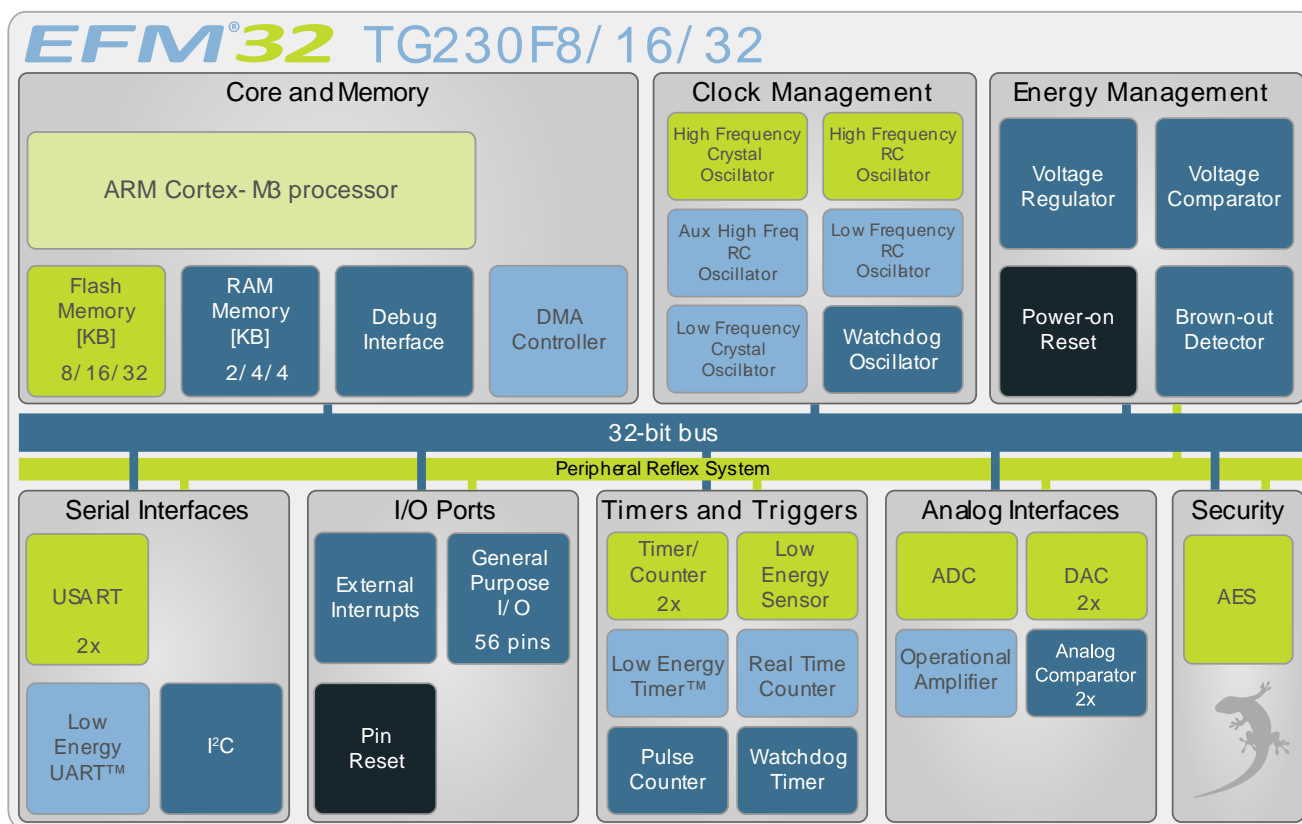
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32TG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32TG230 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32TG Reference Manual*.

A block diagram of the EFM32TG230 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep is included as well. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface . In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32TG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is

2.1.11 Universal Synchronous/Asynchronous Receiver/Transmitter (USART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, IrDA and I2S devices.

2.1.12 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Auto-baud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.13 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUART[™], the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.14 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output.

2.1.15 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.16 Low Energy Timer (LETIMER)

The unique LETIMER[™], the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.17 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.18 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.19 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.21 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.22 Operational Amplifier (OPAMP)

The EFM32TG230 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.23 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.24 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.25 General Purpose Input/Output (GPIO)

In the EFM32TG230, there are 56 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

Figure 2.2. EFM32TG230 Memory Map with largest RAM and Flash sizes

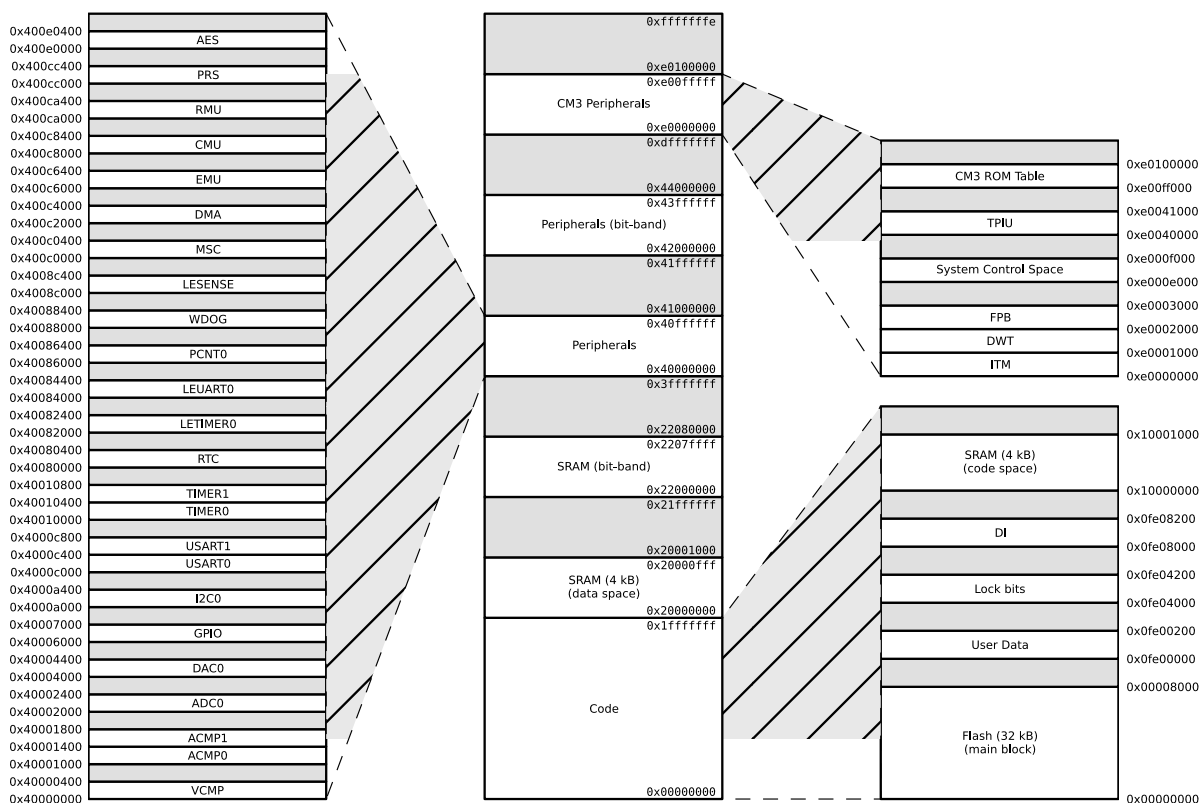
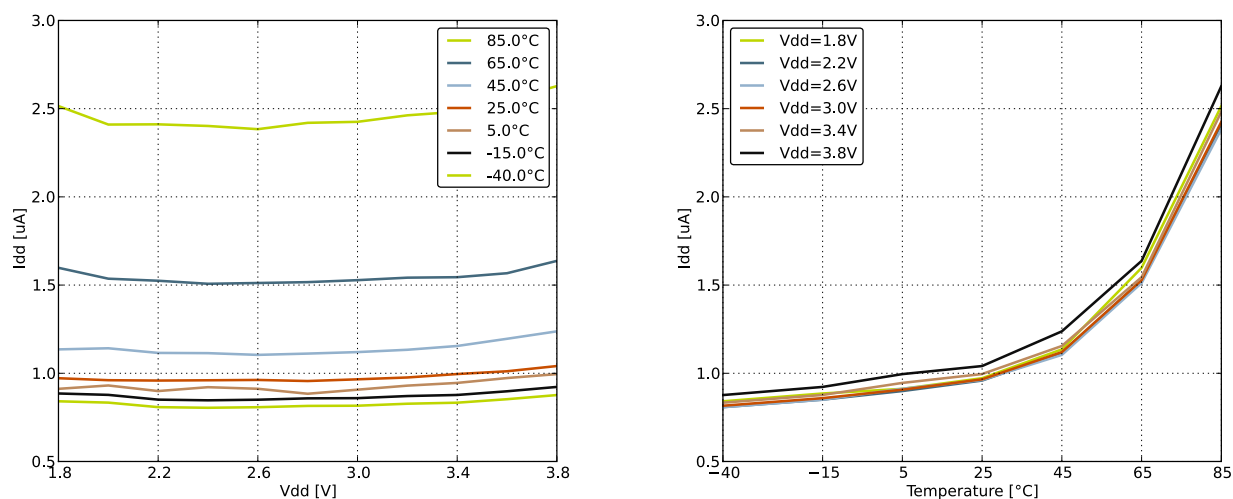
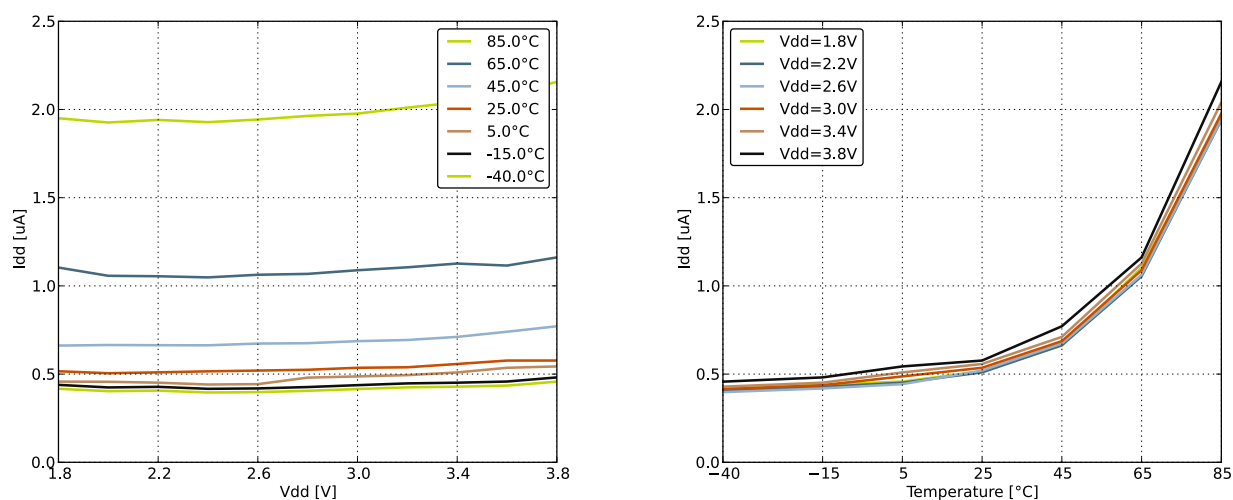
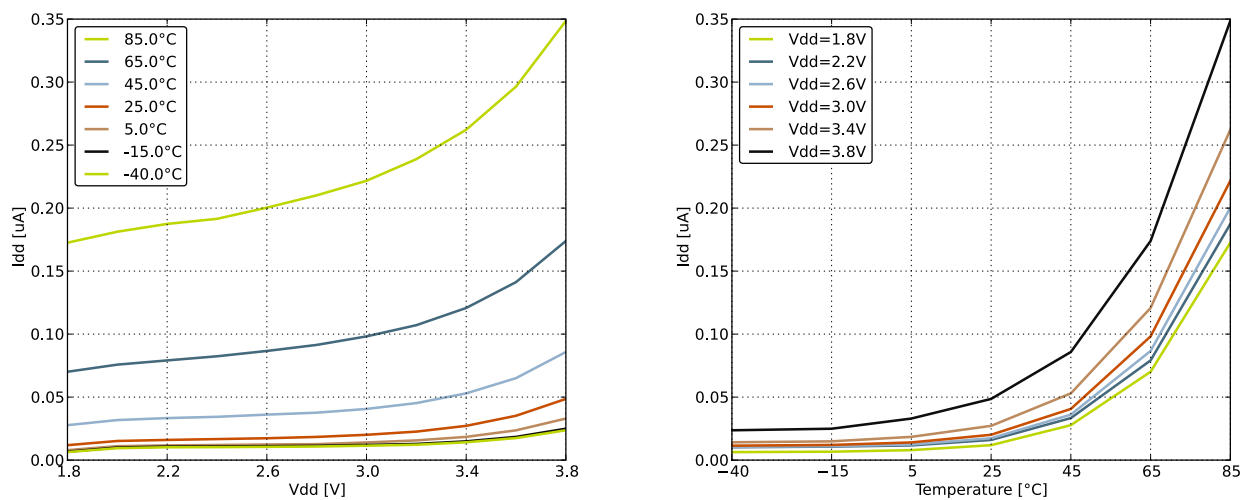


Figure 3.1. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.**Figure 3.2. EM3 current consumption.****Figure 3.3. EM4 current consumption.**

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		\times^1		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

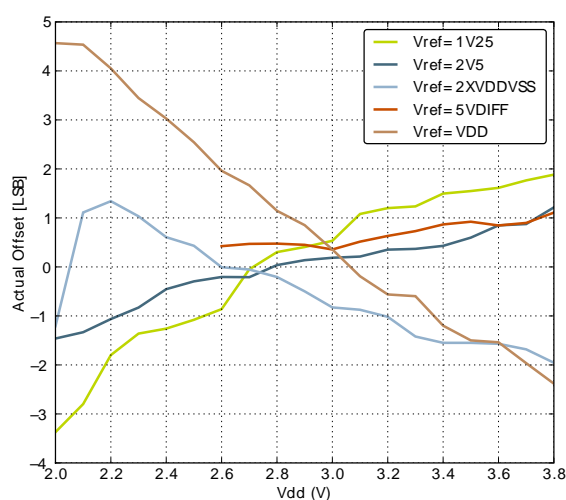
For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

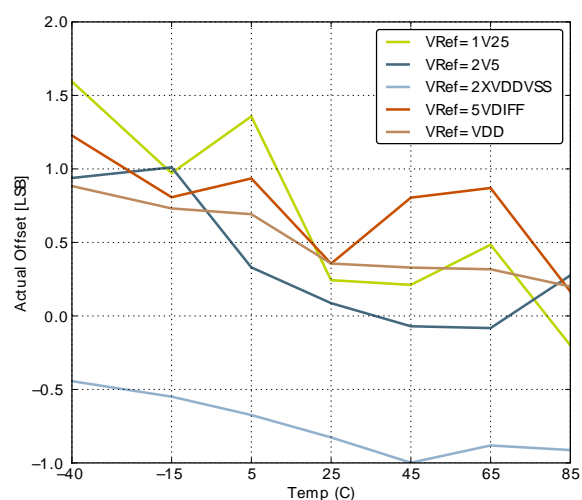
Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		32	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μ A
		32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μ A
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μ s

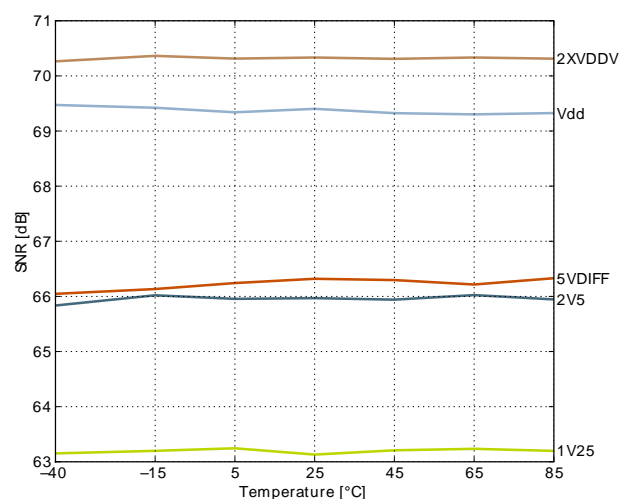
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference		69		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		70		dB
SINAD _{ADC}	Signal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	68		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
SFDR _{ADC}	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc

Figure 3.22. ADC Absolute Offset, Common Mode = $V_{DD}/2$ 

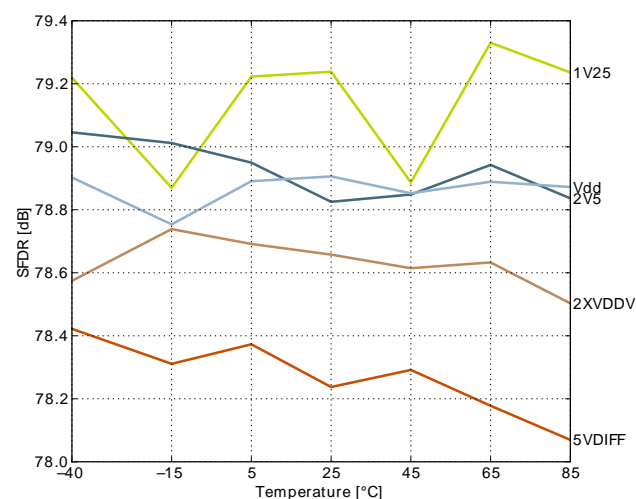
Offset vs Supply Voltage, Temp = 25°C



Offset vs Temperature, VDD = 3V

Figure 3.23. ADC Dynamic Performance vs Temperature for all ADC References, VDD = 3V

Signal to Noise Ratio (SNR)



Spurious-Free Dynamic Range (SFDR)

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12bit		400	650	μA
		100 kSamples/s, 12 bit		200	250	μA
		1 kSamples/s 12 bit NORMAL		17	25	μA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
INL _{DAC}	Integral non-linearity	V _{DD} = 3.0 V, V _{DD} reference		±5		LSB
MC _{DAC}	No missing codes			12		bits

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.16. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{OPAMP}	Active Current	OPA2 BIASPROG=0xF, HALFBIAS=0x0, Unity Gain		350	405	μA
		OPA2 BIASPROG=0x7, HALFBIAS=0x1, Unity Gain		95	115	μA
		OPA2 BIASPROG=0x0, HALFBIAS=0x1, Unity Gain		13	17	μA
G _{OL}	Open Loop Gain	OPA2 BIASPROG=0xF, HALFBIAS=0x0		101		dB
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		98		dB
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		91		dB
GBW _{OPAMP}	Gain Bandwidth Product	OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		16.36		MHz
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		0.81		MHz
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.11		MHz
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		2.11		MHz
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.72		MHz
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.09		MHz
PM _{OPAMP}	Phase Margin	BIASPROG=0xF, HALFBIAS=0x0, C _L =75 pF		64		°
		BIASPROG=0x7, HALFBIAS=0x1, C _L =75 pF		58		°
		BIASPROG=0x0, HALFBIAS=0x1, C _L =75 pF		58		°
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance	OPA0/OPA1	200			Ohm
		OPA2	2000			Ohm
I _{LOAD_DC}	Load Current	OPA0/OPA1			11	mA
		OPA2			1.5	mA
V _{INPUT}	Input Voltage	OPAxHCMDIS=0	V _{SS}		V _{DD}	V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		OPAxHCMDIS=1	V_{SS}		$V_{DD}-1.2$	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, $V_{SS} < V_{in} < V_{DD}$, OPAxHCMDIS=0		6		mV
		Unity Gain, $V_{SS} < V_{in} < V_{DD}-1.2$, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		46.11		V/μs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.21		V/μs
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/μs
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		4.43		V/μs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		1.30		V/μs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/μs
PU_{OPAMP}	Power-up Time	OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		0.09		μs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.52		μs
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		12.74		μs
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		0.09		μs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.13		μs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.17		μs
N_{OPAMP}	Voltage Noise	$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=0		101		μV _{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=1		141		μV _{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		196		μV _{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		229		μV _{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=0		1230		μV _{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=1		2130		μV _{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		1630		μV _{RMS}

3.14 Voltage Comparator (VCMP)

Table 3.18. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{VCMPIN}	Input voltage range			V _{DD}		V
V _{VCMP_{CM}}	VCMP Common Mode voltage range			V _{DD}		V
I _{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	μA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	30	μA
t _{VCMPREF}	Startup time reference generator	NORMAL		10		μs
V _{VCMP_{OFFSET}}	Offset voltage	Single ended		10		mV
		Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			17		mV
t _{VCMPSTART}	Startup time				10	μs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD} \text{ Trigger Level} = 1.667V + 0.034 \times \text{TRIGLEVEL} \quad (3.2)$$

3.15 I2C

Table 3.19. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f _{SCL}	SCL clock frequency	0		100 ¹	kHz
t _{LOW}	SCL clock low time	4.7			μs
t _{HIGH}	SCL clock high time	4.0			μs
t _{SU,DAT}	SDA set-up time	250			ns
t _{HD,DAT}	SDA hold time	8		3450 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	4.7			μs
t _{HD,STA}	(Repeated) START condition hold time	4.0			μs
t _{SU,STO}	STOP condition set-up time	4.0			μs
t _{BUF}	Bus free time between a STOP and START condition	4.7			μs

¹For the minimum HPPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32TG Reference Manual.

²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10⁻⁹ [s] * f_{HPPERCLK} [Hz]) - 4).

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{RTC}	RTC current	RTC idle current, clock enabled		40		nA
I _{AES}	AES current	AES idle current, clock enabled		2.5		μA/ MHz
I _{GPIO}	GPIO current	GPIO idle current, clock enabled		5.31		μA/ MHz
I _{PRS}	PRS current	PRS idle current		2.81		μA/ MHz
I _{DMA}	DMA current	Clock enable		8.12		μA/ MHz

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
30	PD2	ADC0_CH2	TIM0_CC1 #3	US1_CLK #1	
31	PD3	ADC0_CH3 OPAMP_N2	TIM0_CC2 #3	US1_CS #1	
32	PD4	ADC0_CH4 OPAMP_P2		LEU0_TX #0	
33	PD5	ADC0_CH5 OPAMP_OUT2 #0		LEU0_RX #0	
34	PD6	ADC0_CH6 DAC0_P1 / OPAMP_P1	TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2
35	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1	TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2
36	PD8				CMU_CLK1 #1
37	PC6	ACMP0_CH6		I2C0_SDA #2	LES_CH6 #0
38	PC7	ACMP0_CH7		I2C0_SCL #2	LES_CH7 #0
39	VDD_DREG	Power supply for on-chip voltage regulator.			
40	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size C _{DECOUPLE} is required at this pin.			
41	PC8	ACMP1_CH0		US0_CS #2	LES_CH8 #0
42	PC9	ACMP1_CH1		US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
43	PC10	ACMP1_CH2		US0_RX #2	LES_CH10 #0
44	PC11	ACMP1_CH3		US0_TX #2	LES_CH11 #0
45	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			CMU_CLK0 #1 LES_CH12 #0
46	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT	TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0		LES_CH13 #0
47	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT	TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3	LES_CH14 #0
48	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT	TIM1_CC2 #0	US0_CLK #3	LES_CH15 #0 DBG_SWO #1
49	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1
50	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1 GPIO_EM4WU3
51	PF2		TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
52	PF3				PRS_CH0 #1
53	PF4				PRS_CH1 #1
54	PF5				PRS_CH2 #1
55	IOVDD_5	Digital IO power supply 5.			
56	PE8				PRS_CH3 #1
57	PE9				

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
TIM0_CC0	PA0	PA0		PD1	PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	PA1	PA1		PD2	PC0	PF1		Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	PA2	PA2		PD3	PC1	PF2		Timer 0 Capture Compare input / output channel 2.
TIM1_CC0	PC13	PE10		PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11		PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11	PC13			Timer 1 Capture Compare input / output channel 2.
US0_CLK	PE12		PC9	PC15	PB13	PB13		USART0 clock input / output.
US0_CS	PE13		PC8	PC14	PB14	PB14		USART0 chip select input / output.
US0_RX	PE11		PC10	PE12	PB8	PC1		USART0 Asynchronous Receive. USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX	PE10		PC11	PE13	PB7	PC0		USART0 Asynchronous Transmit. Also used as receive input in half duplex communication. USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7	PD2	PF0					USART1 clock input / output.
US1_CS	PB8	PD3	PF1					USART1 chip select input / output.
US1_RX	PC1	PD1	PD6					USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX	PC0	PD0	PD7					USART1 Asynchronous Transmit. Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

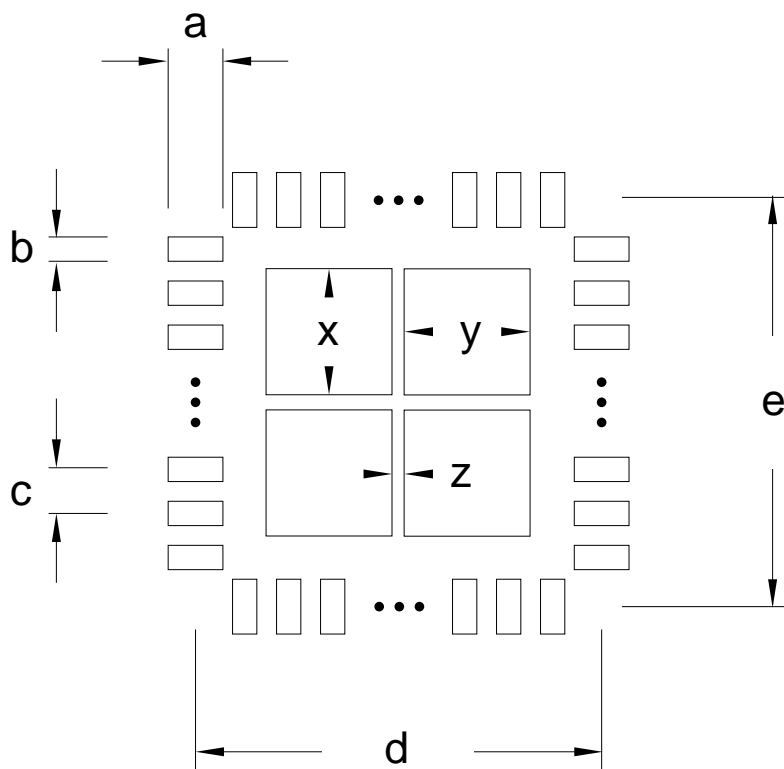
The specific GPIO pins available in *EFM32TG230* is shown in Table 4.3 (p. 51). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	-	-	-	-	PA10	PA9	PA8	-	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	-	PB14	PB13	PB12	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	PC13	PC12	PC11	PC10	PC9	PC8	PC7	PC6	PC5	PC4	PC3	PC2	PC1	PC0
Port D	-	-	-	-	-	-	-	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	PF5	PF4	PF3	PF2	PF1	PF0

4.4 Opamp Pinout Overview

The specific opamp terminals available in *EFM32TG230* is shown in Figure 4.2 (p. 52).

Figure 5.3. QFN64 PCB Stencil Design**Table 5.3. QFN64 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.75	e	8.90
b	0.22	x	2.70
c	0.50	y	2.70
d	8.90	z	0.80

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 52) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

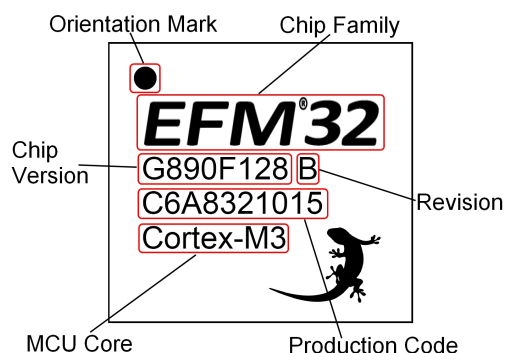
The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions. Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 57) .

6.3 Errata

Please see the errata document for EFM32TG230 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:

<http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit>

7 Revision History

7.1 Revision 1.40

March 6th, 2015

Updated Block Diagram.

Updated Energy Modes current consumption.

Updated Power Management section.

Updated LFRCO and HFRCO sections.

Added AUXHFRCO to block diagram and Electrical Characteristics.

Corrected unit to kHz on LFRCO plots y-axis.

Updated ADC section and added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Updated DAC section and added clarification on conditions for INL_{DAC} and DNL_{DAC} parameters.

Updated OPAMP section.

Updated ACMP section and the response time graph.

Updated VCMP section.

Updated Digital Peripherals section.

7.2 Revision 1.30

July 2nd, 2014

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated current consumption.

Updated transition between energy modes.

Updated power management data.

Updated GPIO data.

Updated LFXO, HFXO, HFRCO and ULFRCO data.

Updated LFRCO and HFRCO plots.

Updated ACMP data.

7.3 Revision 1.21

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.4 Revision 1.20

September 30th, 2013

Added I2C characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Corrected the ADC gain and offset measurement reference voltage from 2.25 to 2.5V.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Document changed status from "Preliminary".

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.5 Revision 1.10

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Added GPIO_EM4WU3, GPIO_EM4WU4 and GPIO_EM4WU5 pins and removed GPIO_EM4WU1 in the Alternate functionality overview table.

Other minor corrections.

7.7 Revision 0.96

May 4th, 2012

Corrected PCB footprint figures and tables.

7.8 Revision 0.95

February 27th, 2012

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level and corrected Thermometer output gradient in Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added reference to errata document.

7.9 Revision 0.92

July 22nd, 2011

Updated current consumption numbers from latest device characterization data.

Updated OPAMP electrical characteristics.

Made ADC plots render properly in Adobe Reader.

Corrected number of DAC channels available.

7.10 Revision 0.91

February 4th, 2011

Corrected max DAC sampling rate.

Increased max storage temperature.

Added data for <150°C and <70°C on Flash data retention.

Changed latch-up sensitivity test description.

Added IO leakage current.

Added Flash current consumption.

Updated HFRCO data.

Updated LFRCO data.

Added graph for ADC Absolute Offset over temperature.

Added graph for ADC Temperature sensor readout.

Updated OPAMP electrical characteristics.

7.11 Revision 0.90

December 1st, 2010

New peripherals added to pinout, including LESENSE and OpAmps.

7.12 Revision 0.60

June 8th, 2010

Corrected pinout.

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